

Radiation	Type	Technology	Electrodes
Red	Diffusion type	GaAsP/GaAs	P (anode) up

	typ. dimensions (μm)	Application This miniature device is an excellent choice for applications where small size and reduced space are important factors such as complex displays in optical devices for laboratory, measurement, control- and medical equipment.
	typ. thickness 330 μm <u>cathode</u> Au-alloy metalization <u>anode</u> Al metalization	

Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Temperature coefficient of λ_C	$T_a = -40..120^{\circ}\text{C}$	$T_C(\lambda_C)$	0.15	nm/K
Operating temperature range		T_{amb}	-40 to +120	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-40 to +125	$^{\circ}\text{C}$

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions ¹	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 5 \text{ mA}$	V_F		1.75	2.0	V
Reverse voltage	$I_R = 10 \mu\text{A}$	V_R	5			V
Luminous intensity/segment ²	$I_F = 5 \text{ mA}$	I_v	55	80		μcd
I_v ratio segment to segment ²	$I_F = 5 \text{ mA}$				1.75	
I_v ratio to adjacent chip	$I_F = 5 \text{ mA}$				2.00	
Peak wavelength	$I_F = 5 \text{ mA}$	λ_p	645	655	665	nm
Spectral bandwidth at 50%	$I_F = 5 \text{ mA}$	$\Delta\lambda_{0.5}$		17		nm

¹Current for one segment

²Measured on bare chip on TO-18 header

Labeling

Type	Lot N°	$I_v(\text{typ}) [\mu\text{cd}]$	$V_F(\text{typ}) [\text{V}]$	Quantity
EDC-660-19-02				

Packing: Chips in wafer pack or on adhesive film with wire-bond side on top

*Note: All measurements carried out with **EPIGAP** equipment